

1 **Table notes: 0**

2 **Revision 3**

3 **Modeling of trace elemental zoning patterns in accessory minerals with emphasis on**
4 **the origin of micron scale oscillatory zoning in zircon**

5
6 Oleg E. Melnik^{1*} and Ilya N. Bindeman²

7

8 ¹Institute of Mechanics, Moscow State University, 119192, 1- Michurinskii prospekt,
9 Moscow Russia

10 ²Earth Sciences, 1272 University of Oregon, Eugene OR 97403

11 *corresponding author melnik@imec.msu.ru

12

13 **Abstract.** We present a numerical model of trace element oscillatory zoning patterns
14 formed when zircon crystallizes from silicate melt which is also appropriate for other
15 accessory phases with known partition and diffusion coefficients and saturation
16 conditions. The model accounts for diffusion-controlled accessory mineral growth and the
17 equilibrium crystallization of major mineral phases. Consideration of recent,
18 experimentally-determined dependencies of partition coefficients on temperature, we find
19 that thermal changes provide the simplest explanations of oscillatory zoning in accessory
20 minerals. Numerical experiments with different cooling rates explore different
21 crystallization scenarios with and without the precipitation of other phases and/or the
22 interface reaction of phosphorus (P) and yttrium (Y) to form xenotime. However, these
23 processes are monotonically related to growth rate and do not cause oscillations. Minor 3-
24 10°C variations in temperature do not result in zircon dissolution, but strongly influence

25 zircon growth and lead to variations in coeval Y, Hf, and rare earth element (REE)
26 concentrations of up to a factor of two, comparable to those observed in nature. Such
27 temperature variations may be very common in any igneous body in response to external
28 factors such as replenishment by hotter magmas or convection. More significant
29 temperature fluctuations may result in initial minor dissolution at higher temperatures
30 during a mafic recharge event but with continuous growth afterwards. At high temperature
31 ($> \sim 850^{\circ}\text{C}$) the amplitude of oscillations is relatively small that confirms observations of
32 both less common oscillatory zoning in hot and dry volcanic rhyolites and abundant
33 oscillations in plutonic zircons and in zircons in cold and wet crystal-rich mushes.
34 Additional oscillations in zircon are modeled in response to oscillations of pressure on the
35 order of $\pm 35\text{-}50$ bars, causing water concentration fluctuations of ± 0.1 wt% in water-
36 saturated melt cells with a gas bubble. These variations cause variations of Zr diffusion
37 and zircon growth rates. Such fluctuations could result from pressure oscillations due to
38 recharge and convection in the magma chamber. All simulated runs generate smoothed
39 oscillatory growth zoning; similar patterns found in nature may not necessarily require
40 post-growth intracrystalline diffusion.

41

42 **Keywords:** Accessory minerals, numerical model, diffusion equation, crystal growth,
43 oscillatory zoning

44

45

1. Introduction

46 **1.1. Oscillatory zoning in minerals**

47 Oscillatory zoning (**Fig. 1**) in igneous minerals is a phenomenon that has
48 fascinated microscopists for more than 150 years (Bunsen, 1851, Bowen, 1928; Corfu et
49 al. 2003). It is typically defined as micron to submicron-scale chemical oscillation and is
50 observed in nearly all accessory minerals of constant composition, and in major minerals
51 (plagioclases, pyroxenes), which are commonly solid solutions. Oscillatory zoning occurs
52 in terrestrial and extraterrestrial (e.g. lunar, meteoritic) objects, in minerals crystallizing
53 from both magmas and hydrothermal solutions. Chemical oscillations affect both major,
54 minor, and trace elements with amplitudes of variation from 10s of percent to a factor of 2
55 to 3. We here distinguish three types of oscillatory zoning that can have different
56 explanations: i) oscillations of major elements in a mineral solid-solution (e.g. plagioclase,
57 pyroxene); ii) oscillations of a minor or trace element in a major phase (e.g. Ti, Al in
58 quartz); and iii) oscillations of trace elements in an accessory phase (e.g. REE in zircon
59 and monazite).

60 Earlier work on oscillatory zoning of major elements in major phases such as
61 plagioclase (Vance, 1962; Wiebe, 1968; Sibley et al. 1976) has resulted in several
62 explanations that invoke both internal and external factors. For major solid solutions
63 (plagioclase, pyroxenes), the partitioning of major components is determined by changes
64 in temperature along liquid lines of descent. However, the solid/melt partition coefficients
65 of major oxides (for example CaO or Al₂O₃ in an albite-anorthite-diopside system (Morse,
66 1994) or in crystallization modeling in MELTS; Ghiorso and Sack, 1995) are ≈ 1 and do
67 not change by more than one order of magnitude between the liquidus and solidus
68 temperatures. The constituent major elements in these minerals have comparable and often

69 coupled (Liang et al. 1994) diffusion coefficients in melts surrounding crystals for all
70 elements, except for ~10 times faster-diffusing alkalis (Zhang et al. 2010).

71 For major minerals with near-constant composition (e.g. Quartz), partition
72 coefficients of oscillating components such as Ti, Al, K, and other recently explored
73 elements are very small ($<10^{-2}$), while their diffusion coefficients are larger than Si (Zhang
74 et al. 2010). An additional feature of these minerals is that the partition coefficient has a
75 very steep and strong dependence on T , which is utilized in several single-element
76 thermometers (Wark and Watson, 2007; Hayden and Watson, 2007; Thomas et al. 2010).
77 These elements occur in the melt in 0.1 to a few wt% levels, and are subject to activity-
78 composition relations affecting the partition coefficient (K) via Henry's Law constants that
79 vary with the activities of other components, a subject of much recent discussion for Ti-in-
80 quartz incorporation (Thomas et al. 2010).

81 This paper is about the zoning of trace elements in accessory minerals (zircon,
82 apatite, rutile and others), minerals commonly of largely constant composition that are
83 very important for geochronology and the trace element evolution of their host magmas.
84 Much work has been performed on zoning in zircon (**Fig. 1**) as revealed by
85 cathodoluminescence imaging (Marshall, 1988). For such accessory phases K and
86 saturation are strong functions of T and depend little on activity-composition relations and
87 on phase diagrams (e.g. Watson and Harrison, 1983), and the following
88 observations/distinctions can be made: 1) the mineral-forming elements for these minerals
89 are commonly trace elements themselves and they do not control the phase relations in the
90 bigger system (e.g. Neogi et al. 2014). 2) The behavior and crystallization of these
91 accessory minerals is simply explained by saturation at a certain temperature and

92 continuing crystallization with decreasing temperature (Watson and Harrison, 1983;
93 Rubatto and Hermann, 2007; Hayden and Watson, 2007). Saturation concentrations are
94 typically very low (hundreds of ppm), leading to very high K values of mineral forming
95 trace elements: 490,000 ppm of Zr in zircon/hundreds of ppm in melt leads to $K = \sim 10^3 - 10^4$
96 for zircon, for example. 3) The diffusion coefficients of their constituting 3+ to 5+
97 elements are typically slower than for silica and other major oxides (e.g. Zhang and Ni,
98 2010). 4) Unlike major phases, the growth rates for most accessory phases are slow and
99 are rate-controlled by slow diffusion of a single minor or trace element of low
100 concentration in the melt: Zr for zircon, P for apatite, REE or P for monazite, Ti for rutile
101 and titanite, REE for chevkinite, etc. These relationships explain why accessory minerals
102 are small and scattered with large spatial separation between major minerals; such
103 relationships justify the use of a simple 1D diffusion-growth model in spherical
104 coordinates with two moving boundary conditions that we employ here (**Fig. 2**). The rest
105 of discussion will be centered on zircon (**Fig. 1**), but the conclusions should be applicable
106 to other accessory phases.

107

108 **1.2. Trace element partitioning in zircon, element coupling, and co-crystallization of** 109 **other phases**

110 Trace elements entering zircon obey Onuma-type partitioning relationships (e.g.
111 Hanchar et al. 2001; Hanchar and van Westrenen, 2007) with elements of the same
112 valence group and with sizes closest to those of the sites of preferred substitution (e.g. Hf)
113 having far greater partition coefficients than smaller or larger ions (e.g. Ti). The variations
114 in trace element concentrations do not change the Henry's Law constant, K , although for

115 elements with a concentration of just a few ppm, such as Ti in zircon, defect site
116 partitioning has been proposed (Fu et al. 2008).

117 REE, Y, Sc other 3+ elements, and also 5+ elements require charge compensation
118 when diffusing in the 4+ crystal structure of zircon. Entry of both REE and 5+ elements
119 into zircon is commonly explained by xenotime-type substitution, $P^{5+} + Y^{3+} = Si^{4+} + Zr^{4+}$,
120 that should lead to a 1:1 covariant line of P and Y concentrations (Hanchar et al. 2001).
121 Reviewing the literature and from our own considerations below, we cannot say with
122 certainty that trace element coupling is the controlling phenomenon in trace element
123 partitioning, due to the exceedingly low abundances of trace elements. Furthermore, many
124 studies of natural samples have demonstrated both molar excess and deficiencies of P with
125 respect to SUM ($REE^{3+} + Y^{3+}$) suggesting that xenotime-type substitution is not the only
126 possibility for Y and P entrance into zircon (Finch et al. 2001). DeHoog et al. (2014)
127 suggested that H^+ plays an important role in charge compensation and promotes the
128 partitioning of trace elements into zircon and Trail et al. (2016) considered the role of Li.
129 An alternative explanation is the independent entry of trace elements generates vacancies
130 into zircon in accordance to the Henry's Law constants of each element.

131 A way to empirically test for coupling, or a lack thereof, in element partitioning is
132 to consider elemental covariations in oscillatory zoned zircons (**Fig. 1**). For illustrative
133 purposes in this study we performed measurements of trace elemental variations in zircons
134 from silicic systems spanning from cold, near solidus conditions to hot, near liquidus
135 conditions, the Fish Canyon Tuff, Young Toba tuff, and major Yellowstone tuffs,
136 respectively (**Fig. A1**). Our measurements agree with previous data and are suggestive of
137 covariation between elements, but without a 1:1 relationship. These considerations also

138 have implications for the origin of elemental zoning patterns, and in particular on whether
139 such coupling leads to oscillations. An additional important factor in generating trace
140 elemental variations in zircons is the co-crystallization of additional phases that happen to
141 partition the very same elements. This process commonly occurs in nature (e.g. zircon
142 co-crystallizing with sphene and apatite). For example, if crystallization of apatite happens
143 together with zircon, the residual melt as well as zircon may become depleted in P.
144 However, the rate of “signal” transfer from apatite to zircon (i.e. P concentration in the
145 melt) will be dependent on the diffusion coefficient of P and the mean distance between
146 zircon and apatite crystals. Crystallization of both accessory phases is controlled by simple
147 saturation conditions rather than by complex reactions, and so saturation and rates of
148 diffusion are controlled by temperature, which in turn controls trace element/melt
149 partitioning coefficients.

150 We thus search for the simplest physical explanation of oscillatory zoning
151 phenomena by considering temperature and water content fluctuations and their effect on
152 experimentally-determined saturation conditions, and diffusion, and partition coefficients.
153 We explore if this simplest model is sufficient to explain patterns of trace element
154 distribution in zircon, including 1) the length scale, amplitude, and relative position of the
155 modeled elements, 2) the magnitude of temperature changes that are required to explain
156 naturally observed mineral zoning, and 3) the influence of the co-crystallizing major
157 phases. Then we devote attention to the effect of coupled substitutions and show that if
158 present, these does not lead to compositional oscillations.

159

160

2. Model

161 2.1 Mathematical model

185 Here C_i is the concentration of i -th element, measured in ppm, r is the radius counted from
186 the center of the zircon crystal, and t is the time. Eq. (1) is solved only inside the melt part
187 of the cell, $s < r < R$, because the diffusion of Zr and trace elements in the crystal phase is
188 very slow in comparison with diffusion in the melt.

189 Boundary conditions at the crystal-melt interface ($r = s$) ensure local
190 thermodynamic equilibrium, mass conservation of Zr and trace elements, and the partition
191 of trace elements.

$$192 \quad r = s : -D_i \left. \frac{\partial C_i}{\partial r} \right|_{r=s} = J_i = V [C_i^m - C_i^s]; \quad C_{Zr}^m = C_{sat}(T), C_{Tr}^s = K(T) C_{Tr}^m. \quad (2)$$

193 Here V is the linear growth rate of zircon, C_i^m is the concentration of Zr and trace
194 elements in the melt attached to the growing zircon crystal, C_{Tr}^s is the trace element
195 concentration in zircon, and $C_{Zr}^s = 490,000$ ppm is Zr concentration in zircon. The
196 saturation concentration C_{sat} of Zr mainly depends on temperature and melt composition
197 which are governed by equations in Watson and Harrison (1983) and Boehnke et al.
198 (2013) and integrated into the model. In the simulations presented below we use Boehnke
199 et al. (2013) formulation with the value of M-factor equal to 1.62 appropriate for low
200 silica "monotonous intermediate" felsic magmas that exhibit oscillatory zoning. $K(T)$
201 values are the partition coefficients of trace elements of interest between the melt and the
202 zircon crystal.

203 On the outer melt boundary ($r = R$), mass partitioning of Zr and trace elements
204 between major minerals and the melt is specified:

$$205 \quad r = R : -D_i \left. \frac{\partial C_i}{\partial r} \right|_{r=R} = J_i = W [C_{m,i} - C_{X,i}]; \quad C_{X,i} = k C_{m,i}. \quad (3)$$

206

207 Here W is the velocity of the outer boundary controlled by changes in the melt fraction
208 due to crystallization of major minerals, C_X is the concentration of zirconium and trace
209 elements in major minerals, and k is the distribution coefficient $C_{Zr}^{major}/C_{Zr}^{melt}$. In order to
210 determine W we use phase diagram (solidus-liquidus) relations for a typical granitic melt
211 after the crystallization experiments of Piwinskii (1968, composition 102 at 2 kb):

$$x = 3.1\Theta - 8.9\Theta^2 + 12.3\Theta^3 - 5.46\Theta^4,$$
$$\Theta = \frac{T - T_s}{T_L - T_s}, T_s = 973 K, T_L = 1203 K. \quad (4)$$

213 Here x is the melt fraction and Θ is the dimensionless temperature. A discussion of the
214 effect of changing the parameters in eq. (1-3) will be presented below.

215 The current model that monitors trace element concentrations and behavior within
216 zircon does not allow for the modeling of zircon dissolution, because it does not store the
217 trace element distribution within zircon. Thus, it cannot calculate mass balances for trace
218 elements (eq. 2) correctly for negative values of the velocity, V , as linear partitioning
219 between the melt and the crystal does not work during dissolution. However, the present
220 model as is shown below is able to simulate zircon oscillatory zoning with slow growth
221 rather than by zircon dissolution.

222 **2.2. Properties of species: diffusion and partitioning relations**

223 As zirconium diffusion in melt is strongly dependent on temperature and water
224 content (Watson and Harrison, 1983), we use the parametrization from Bindeman and
225 Melnik (2016) for the Zr diffusion coefficient D_{Zr} and the equilibrium melt saturation
226 $C_{sat}(T)$ as:

227
$$\ln(D_{Zr}) = -\frac{11.4X_{H20} + 3.13}{0.84X_{H20} + 1} - \frac{21.4X_{H20} + 47}{1.06X_{H20} + 1} \cdot \frac{1000}{T} \quad (5a) \quad (5b)$$

228
$$C_{sat} = 490000 / \exp\left(\frac{10108}{T} + 1.16(M - 1) - 1.48\right)$$

228 As this work considers not only zircon growth but also the incorporation of other
229 elements in zircon, diffusion coefficients for Zr and other trace elements in the melt are
230 taken from a compilation by Zhang et al. (2010). **Figure 3a** shows the values of trace
231 element diffusion coefficients normalized to Zr diffusion coefficient at $X_{H20}=3$ wt.%. We
232 assume that Dy^{3+} and Y^{3+} diffusion coefficients are equal. Ti^{4+} is the fastest diffusing
233 element followed by Zr^{4+} , then Y^{3+} , Dy^{3+} , other REE^{3+} , and Hf^{4+} are within one log unit
234 from Zr^{4+} , and finally P^{5+} , U^{4+} and Th^{4+} are significantly slower. This order is in line with
235 the faster diffusion of smaller, lesser charged elements in silicate melts (e.g. Hahn et al.
236 2005).

237 Partition coefficients of the trace elements between zircon and silicic melt are
238 presented in **Fig. 3b** and range from ~ 4 for P to more than 3000 for Hf (Rubatto and
239 Hermann, 2007). The Rubatto and Hermann (2007) experiments were conducted at lower
240 temperatures (800-1000°C) than many previous ones dealing with zircon saturation (e.g.
241 Harrison and Watson, 1984), and extrapolation of partition and saturation data to the
242 lowest (650-750°C) T is still required. We note the steep dependence of partition
243 coefficients on temperature for most elements with the steepest dependence being for Y,
244 as has been noted before in many other experiments involving accessory phases (e.g.
245 monazite, apatite, garnet, Zhang et al., 2010).

246 Coupled substitution of major and trace elements of different valence groups (e.g.
247 $P^{5+} + Y^{3+} = Si^{4+} + Zr^{4+}$) in zircon is much discussed topic, with natural and experimental

248 evidence both supporting and contradicting it (Hanchar et al 2004; Hoskin and
249 Schaltegger, 2009; Trail et al; 2016 and references therein). To see if coupled substitution
250 matters for oscillations, we defined the boundary conditions to allow and disallow coupled
251 substitution at the growing zircon surface. With respect to diffusion in the silicate melt,
252 different trace elements diffuse independently as there are several charge compensating
253 mechanisms in the melt involving major elements (e.g., Zhang et al., 2010). Elemental
254 groups or cluster formation in the vicinity a zircon-melt interface where 3+ and 5+ and 1+
255 elements compete is of much interest (Rustad, 2015), but has not been determined with
256 certainty. In the present numerical model, we treat each element independently with
257 respect to its experimentally-determined diffusion and partition relations as is shown in
258 **Fig. 3**. Expressions for trace element diffusion and partition coefficients can be found in
259 supplementary MATLAB code (functions TraceDiff and Kdd, respectively). In section 3.2
260 we explore the effect of coupled P and Y incorporation into the zircon.

261 Diffusion of 3+, 4+ and 5+ trace elements in zircon is too slow (Cherniak et al.
262 1997a, b) to affect their distribution on volcanic and even plutonic timescales, and in the
263 modeling below we ignore trace elemental redistribution in zircon upon capture. Some
264 diffusional relaxation of the originally step-function or sawtooth profile in zircon is
265 possible on submicron scales, especially in hotter and longer-lived systems given these
266 published diffusion coefficients, but this will not affect the observed zonation on larger
267 scales.

268 **2.3 Numerical algorithm**

269 The model was written in MATLAB and used an unconditionally stable implicit
270 formulation for the discretized diffusion equation in a fixed frame domain by using a tri-

271 diagonal matrix (Thomas method) algorithm. Details of the numerical method are
272 presented in Bindeman and Melnik (2016) for pure zircon growth. We solve Eq. (1) with
273 boundary conditions (2,3) independently for each trace element. Zircon growth rates are
274 obtained from the solution of the diffusion equation for zirconium. Changes in the melt
275 fraction and the corresponding velocity of the outer cell boundary are governed by
276 temperature changes only along specified phase diagram given by Eq. (4).

277

278 **3. Results**

279 **3.1 Zircon crystallization from melt and partitioning relations during** 280 **monotonic cooling**

281 We first consider a scenario of zircon crystallization from a melt cooling at a
282 constant rate in order to detect any oscillatory zoning of trace elements naturally resulting
283 from crystallization histories of their host magmas in the framework of our model. **Figure**
284 **4** shows calculated profiles in the melt for normalized concentrations of Zr (dashed line)
285 and trace elements at the final temperature for the simulation of zircon growth during a
286 linear temperature drop from 840 to 720°C over 5000 years from a 2 mm melt cell with no
287 major mineral crystallization ($W=0$, **Fig. 2**). As the temperature decreases the zircon starts
288 to grow and a diffusive boundary layer with a decreased concentration of Zr and other
289 strongly compatible elements (the “trough”) is formed and persists for the entire duration
290 of crystallization in all models.

291 The zircon growth rate is determined by the diffusion of zirconium towards the
292 crystal-melt interface (e.g. Harrison and Watson, 1984). Both the diffusion and partition
293 coefficients play a role in the formation of boundary layers in trace element

294 concentrations. The boundary layer is strongly depleted in Hf because its partition
295 coefficient is large and its diffusion is slower than that for Zr. U diffuses faster than Th,
296 but has much higher partition coefficient resulting in stronger depletion in the boundary
297 layer. Dysprosium and Y diffuse at the same speed in our model, but Y is more
298 compatible than Dy, thus the boundary layer is more strongly depleted in Y. P, which has
299 a small diffusion coefficient similar to U, is only slightly compatible in zircon and remains
300 relatively concentrated in the melt phase adjacent to the zircon despite its slow diffusion.
301 If the temperature stops decreasing at $T = 800^{\circ}\text{C}$ in our model, the depletion disappears in
302 ~ 5 ka, making it possible to detect last stage of zircon growth if it is quenched later due to
303 a rapid T drop or H_2O loss (which affects diffusion coefficients of Zr dramatically, as
304 Bindeman and Melnik (2016) documented in glasses adjacent to zircon the Summit Lake
305 flow of Yellowstone; **Fig. 18**).

306 Because all modeled trace elements (excluding P and Ti) have $K \gg 1$ in zircon, no
307 piling up effects are possible for zircon and other accessory minerals with similar
308 partitioning near the boundary. Indeed, the opposite may be true resulting in boundary
309 layer depletion. This simple consideration of high K and slow diffusion eliminates one
310 possible mechanism of oscillatory zoning in accessory phases, that is otherwise suggested
311 for plagioclase, for example, (e.g., Sibley et al. 1976). However, bulldozing effects can be
312 present on the outer melt boundary and lead to a piling up of trace elements as a function
313 of W and k . (**Fig. 2** also see Bindeman and Melnik, 2016). Oscillatory temperature
314 changes cause crystallization of the major minerals on the outer boundary (**Fig. 2**), causing
315 the propagation of compositional diffusion waves towards the growing zircon in the
316 center. However, these compositional waves are modulated by the relatively long distance

317 in melt cell around the zircon, and the slow elemental diffusion on short timescales. Thus,
318 major element growth oscillations due to crystallization of a major mineral are dampened,
319 and compositional “waves” from major element growth oscillations are not reflected in
320 zircon zoning.

321 **Figure 5** shows the distribution of trace elements within the zircon crystal as a
322 function of its radius. High diffusivity and a sharp increase in the partition coefficient of Y
323 with a decrease in temperature result in the enrichment of the zircon crystal in Y as
324 crystallization proceeds. The large partition coefficient and relatively slow diffusivity of
325 Hf result in the depletion of the boundary layer in Hf and a consequent decrease in the Hf
326 concentration in the growing zircon. There are also smaller increases in U, Th, and P
327 towards the zircon rim due to an increase in partition coefficient at low temperatures (**Fig.**
328 **3b**).

329 Another important trace element that enters the zircon structure is Ti, which is
330 used in many other geochemical and geothermometry studies (e.g. Ferry and Watson,
331 2007). We plot for reference the variation of Ti content in zircon using Eq. (15) from
332 Ferry and Watson 2007 with activities of SiO₂ and TiO₂ equal to 1 and 0.65, respectively,
333 as is accepted by the above authors. There is a progressive decrease in Ti concentration
334 within zircon during crystallization and at lower temperatures as Ti is a fast diffuser
335 compared to Zr and zircon growth does not produce elevated concentrations at the
336 boundary layer, despite Ti’s small partition coefficient.

337 It is important to note that our numerical modeling assuming monotonic
338 temperature decreases from high to low T along a linear path produces no sign of
339 oscillatory zoning. This result holds in a wide field of parameter space and is independent

340 of the cooling rate (ranging from 10° to 0.01°C/yr). Further experimentation with non-
341 linear but smooth temperature paths, characteristic of cooling intrusions, ranging from
342 concave-down exponential to concave-up square root also show no sign of oscillatory
343 zoning. This is simply explained by the absence of a feedback between boundary layer
344 concentrations of trace elements and the zircon growth rate, which is controlled solely by
345 the diffusive flux of Zr. Zircon itself grows monotonically with respect to cooling in our
346 numerical experiments (this work and Bindeman and Melnik, 2016).

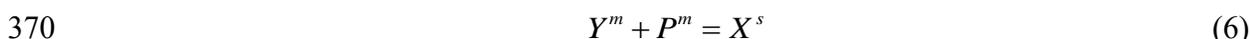
347 The numerical simulations presented above show large (up to 0.4 wt%),
348 concentrations of P (**Fig. 5**) in zircon at the later stages of the growth due to larger values
349 of the partition coefficient of P at low temperatures (see **Fig. 3b**). The increase in P
350 content is comparable to Y, in agreement with data where both elements are measured
351 (e.g., Aranovich et al. 2016), although Y and P commonly show a variety of zoning
352 patterns (Hoskin and Schaltegger, 2009; Hanchar et al. 2001a,b ; Hoffman et al. 2009;
353 Trail et al. 2016). There are several possible explanations for this. First, partition
354 coefficients of P in zircons and their *T* dependence are poorly known, and, second, the
355 simultaneous growth of apatite, which always co-precipitates with zircon, will reduce the
356 phosphorus content in the melt to the apatite saturation level, and consequently the P
357 concentration in zircon will drop down.

358

359 **3.2 Interface kinetic reactions**

360 The incorporation of P and Y into zircon may not be completely independent from
361 one another, as is proposed in many studies (Hoskin and Schaltegger, 2009 and references
362 therein) under the xenotime-type substitution mechanism $Y^{3+} + P^{5+} = Si^{4+} + Zr^{4+}$. If so, the

363 very high partition coefficients predicted by extrapolation of high-T to low-T data (**Fig. 3**)
364 may be mitigated by the interface-xenotime formation reaction that we now consider. If
365 the interface exchange reaction plays an important role for the entry of heterovalent
366 elements into zircons, then other charge compensating mechanisms described in the
367 introduction may also lead to the outcome that elements influence each other's
368 partitioning relations. Here, we model xenotime substitution into zircon, which is
369 explained by its formation reaction:



371 We assume that xenotime does not independently nucleate in the melt because Y
372 concentration is low, but rather forms only at the zircon's surface during incorporation
373 into the crystal where the concentrations of Y is the highest due to the very high partition
374 coefficient (**Fig. 3b**), and thus reaction (6) is shifted to the right at the surface of zircon,
375 where xenotime likely forms in nanoclusters. The formation and destruction of the
376 xenotime can be modeled with forward and reverse reaction constants of the first order
377 reaction, k_f and k_r .

378 To check if P and Y coupled substitution can cause oscillatory zoning of the
379 xenotime component in zircon we use the results from a linear temperature drop run and
380 solve diffusion equations for P and Y with modified boundary conditions:

$$381 \quad \begin{aligned} -D_i \frac{\partial P}{\partial r} \Big|_{r=s} &= V [P^m - P^s] - \frac{(k_f PY - k_r X)}{2}; \quad P^s = K_P(T) P^m, \\ -D_i \frac{\partial Y}{\partial r} \Big|_{r=s} &= V [Y^m - Y^s] - \frac{(k_f PY - k_r X)}{2}; \quad Y^s = K_Y(T) Y^m, \\ \frac{\partial X^s}{\partial t} \Big|_{r=s} &= k_f PY - k_r X - VX^s, \quad X^s = K_x(T) X^m. \end{aligned} \quad (7)$$

382 Here P , Y and X are the concentrations of phosphorus, yttrium and xenotime, respectively,
383 and k_f and k_r are the reaction rates for the forward and reverse reactions of xenotime
384 formation and dissociation. We assume that xenotime is unstable (not saturated) far from
385 the zircon-melt interface and, thus, we do not solve the diffusion equation for X in the
386 melt. Yttrium and P diffuse independently to the boundary and xenotime is only formed in
387 the very narrow surface boundary layer adjacent to zircon. For this simulation, we can
388 assume that only xenotime can be incorporated into the zircon structure. In this case the
389 partition coefficients of P and Y, K_P and K_Y , are equal to zero. As an initial condition we
390 assume an equilibrium xenotime concentration: $X(t=0) = k_f P(0) Y(0) / k_r$.

391 **Figure 6** shows the xenotime distribution within the zircon for different values of
392 K_X for $K_P = K_Y = 0$. Due to the decrease in Y concentration in the melt, the formation of
393 xenotime progressively slows down resulting in lower concentrations of X in the zircon as
394 the crystal grows. The decrease in concentrations of both P and Y occurs monotonically
395 but we do not observe oscillations with respect to either element. Thus, the coupled
396 substitution of P and Y cannot be a cause of oscillatory zoning in zircon as the interface
397 exchange reaction is *linearly* proportional to the concentrations of the elements or their
398 products as is explained in Eq. (6). However, this mechanism of coupled substitution may
399 help mutual partitioning of P and Y, especially when there is a 1:1 molar relationship as is
400 observed in some studies (Hoskin and Schaltegger, 2003).

401

402 3.3. Temperature oscillation effects on growth rates and Zr concentrations

403 Next, we investigate how small temperature variations can result in non-monotonic
404 changes in crystal composition and zircon zoning patterns. A series of simulations with a
405 sinusoidal temperature drop (Eq. 8) was performed:

$$406 \quad T(t) = T_0 - qt - \Delta \sin(\omega t). \quad (8)$$

407 Here T_0 is the initial temperature, q is the cooling rate, Δ is the amplitude of the
408 temperature oscillations, ω is the frequency, and t is the time. We assume that 20 periods
409 of temperature oscillations occur during melt crystallization, which is sufficient to
410 understand the nature of the process, and also corresponds to the order of the number of
411 observed oscillatory zones in natural zircons (e.g., **Fig. 1**).

412 **Figure 7** shows the evolution of the zircon radius (a) and growth rate (b) for the
413 temperature history given by Eq. (8) over the total cooling time (in kyr). The total duration
414 of these numerical experiments ranges from 500 to 50,000 years (corresponding to
415 average cooling rates of 0.25°C/yr to 0.0025°C/yr). It results in a zircon of smaller size at
416 the faster cooling rate, largely because when temperature drops rapidly, the diffusion of Zr
417 in the melt slows and the zircon does not grow as large due to diffusion limitation. For
418 average cooling rates of <0.025°C/yr, zircons grow to a radius of 65-80µm. It is a notable
419 result of our simulations that small to moderate temperature oscillations of several °C do
420 not lead to zircon dissolution at any cooling rates, but instead lead to a decreased growth
421 rates in zircon (**Fig. 7b**). This happens because Zr concentrations in the boundary layer are
422 initially very low in the boundary layer (trough) around the growing crystal. With a T
423 increase, the concentration at the interface $C_{sat}(T)$ starts to increase to a new C_{sat} level
424 corresponding to the increasing temperature. However, the diffusive flux fills the deep

425 trough making it shallower while the concentration gradient near boundary remains
426 negative, which according to Eq. (2) keeps the zircon growth velocity (V) positive, leading
427 to decelerated zircon growth. When the concentration near the boundary becomes flat,
428 zircon growth stops. It is therefore the slow diffusion of Zr that damps (modulates) small
429 T oscillations in a melt cell surrounding zircon. We further experimented with a larger ΔT
430 amplitudes of oscillation of $\geq 10^\circ\text{C}$ and observed that for a 50ky cooling time ΔT needed to
431 be more than 10°C to stop zircon growth ($V = 0$) and begin dissolution during oscillations.
432 In the case of a 0.5 ky cooling time, only during the first two temperature cycles is zircon
433 dissolution observed for the amplitude 10°C of temperature fluctuation. When the
434 temperature drops rapidly to low values, the Zr gradient (**Fig. 4**) in the boundary layer
435 becomes too large to overcome, preventing zircon dissolution during the next temperature
436 increase. Higher temperatures and faster Zr diffusion at higher $\text{H}_2\text{O}_{\text{melt}}$ lead to a shallower
437 trough near the zircon-melt boundary, (Eq. 5, **Fig. 3**). For lower T systems with slow Zr
438 diffusivities, lower water, and for quicker cooling times, the concentrational troughs
439 around growing zircons are deeper (**Fig. 4**). For such systems, there is a greater tolerance
440 to stronger ΔT oscillation of $10\text{-}20^\circ\text{C}$ of continuing zircon growth without causing zircon
441 dissolution.

442 There is a progressive decrease in the growth rate as the temperature decreases due
443 to a decrease in Zr supply to the growing crystal as diffusion slows down at lower
444 temperatures. Marked oscillations in the growth rate are caused by changes in the Zr
445 equilibrium concentration with temperature (5 to 10 ppm of Zr in melt for the temperature
446 change $\pm 3^\circ\text{C}$). Changes in the Zr concentration at the interface affect the concentration
447 gradient strongly and, as a consequence of the boundary condition (Eq. 2), the growth rate

448 of the crystal. Stronger oscillations of the growth rates at low cooling rates are caused by
449 the ability of Zr to diffuse in and out of the boundary given longer timescales between
450 oscillations.

451

452 **3.4. Temperature oscillations effects on Hf and Y partition**

453 **Figure 7** (c and d) shows the profile of Hf and Y concentrations in zircon as an
454 example of trace element concentrations in zircon reacting to temperature oscillations.
455 Other elements will show similar but less prominent behavior and are considered in **Fig. 8**.
456 The Hf concentration is low in the boundary layer during periods of rapid zircon growth at
457 any growth rate due to its strong partitioning into zircon (see **Fig. 4**). With each periodic
458 increase in temperature along the cooling path, the growth rate decreases. Thus, the
459 diffusion of Hf from the vicinity of the melt to the boundary layer leads to an increase in
460 the Hf concentration at crystal-melt interface and, following partition relationships, the Hf
461 concentration in the crystal. On the local minima of the ΔT oscillation, the zircon growth
462 rate increases and the Hf content in the boundary layer drops down rapidly to a deep
463 through.

464 There is also an important difference in the influence of temperature oscillations at
465 different cooling rates as observed in the models over 0.5, 5, 25 and 50 ka for an 840 to
466 720°C temperature decrease. For faster cooling (840 to 720°C in 0.5 and 5 ka, green and
467 blue curves, **Fig. 7**), zircon crystals are smaller. The supply of Hf to the boundary layer is
468 not efficient because of the slow diffusion at low temperatures and the overall Hf content
469 in the crystal progressively decreases from core to rim (compare with **Fig. 5**) in spite of
470 increase in the partition coefficient. At lower cooling rates, the Hf partition coefficient

471 increase dominates leading to an overall increase in Hf concentration towards the crystal
472 rim. Natural zircons typically have an increase in Hf concentrations toward the rim
473 (Claiborne et al. 2017) with Zr/Hf ratio of about 1.3. This may indicate that many zircons
474 studied by these authors reflect relatively slow cooling conditions.

475 At any cooling rates, but more so for slow cooling, Hf oscillatory zoning in zircon
476 is wide in the core (zones of up to 10 μ m wide) and narrower (~1 μ m wide) in the rim
477 because zircon growth rates decrease at low temperatures and the amount of growth
478 during one temperature cycle becomes smaller. This effect is independent on the simple
479 radius-volume relationship on decreasing of thickness of growth zones with increasing
480 radius from the center of zircon. This is a common observation in zoning patterns within
481 natural zircons and other accessory minerals in which cores are rather homogenous (and
482 often with sector zoning, also signifying faster growth; Liang and Watson, 1995; **Fig. A2**,
483 supplementary) and rims are finely zoned (**Fig. 1**; Corfu et al., 2003; Hoskin and
484 Schaltegger, 2009).

485 Furthermore, the shape of the Hf oscillations and concentration profiles in zircon
486 are different in the cases of fast and slow cooling. At slow cooling, higher concentrations
487 of Hf have sharp terminations at inflection points, and at fast cooling rates oscillatory
488 zoning is more sinusoidal and similar to the ΔT vs time function (Eq. 8). These predictions
489 are an important result for current and future imaging efforts of zircon oscillations by
490 either electron microprobe or NanoSIMS (**Fig. 1**, A1, Hoffman et al., 2009) as analytical
491 capabilities to image the shapes of individual oscillations at sub-micron level increases. A
492 prediction from our work is that sharp terminations result from slow but large ΔT
493 variations while smoothed oscillations in trace element concentrations may not necessarily

494 reflect post-entrapment diffusional relaxation but rather be a prime growth feature at
495 relatively fast (e.g. $>0.02^{\circ}\text{C}/\text{yr}$) cooling rates.

496 **Figure 7d** demonstrates the evolution of Y concentrations in zircons for different
497 cooling rates. Y is also an analogue for the behavior of the mid-heavy REEs considered
498 below. Due to fast diffusion and a steeper K_d vs $1/T$ partition dependence (than for Hf, see
499 **Fig. 3**), Y concentration in zircon progressively and dramatically increases to 1.5 wt%
500 from the core to the rim of the modeled zircon (**Fig. 7**) at any studied cooling histories.
501 Furthermore, the faster diffusion of Y (**Fig. 3a**) as compared to Zr and Hf, makes it
502 respond to changes in growth rate more rapidly, and the Y concentration in the crystal
503 more closely reflects the local crystal-melt equilibrium at any given temperature
504 (shallower troughs on **Fig. 4**). Y rim concentration slightly increases with the increase in
505 overall cooling time. Additionally, the resulting oscillations are always more sinusoidal
506 and symmetric than for Hf.

507

508 **3.5 Temperature oscillation effects on other trace elements**

509 **Figures 8a-c** demonstrate variations in Hf, Y, U, Th, P and Dy for the same linear
510 cooling over 0.5, 5, 25 and 50 ky from 840 to 720°C as is described in **Fig 7a**. Many
511 observations related to oscillatory zoning patterns (width, amplitude, shape, terminations)
512 for Hf and Y, hold for the other elements as a function of their partition and diffusion
513 relations (**Fig. 3**): elements with slower diffusion (P, Y, U, Th) exhibit a sawtooth pattern
514 of oscillations in contrast to more sinusoidal zoning for other, faster diffusing elements.
515 Also notice that the width of oscillatory zones coincides for all of the elements despite
516 them having rather different (± 1 order of magnitude) diffusion coefficients in melt (**Fig.**

517 **3a).** This result suggests that oscillations are mostly controlled by the frequency of
518 temperature oscillations and zircon growth rates during each period rather than rates of
519 diffusion of trace elements in the melt. Coeval oscillations of elements are commonly, but
520 not universally observed in natural zircons analyzed and profiled in situ, (**Fig. 1**; Claiborne
521 et al. 2017), and should apply to zircons with simple growth histories.

522 The overall amplitude of trace elemental fluctuations of the concentrations of other
523 trace elements are significantly smaller in comparison with Hf. The amplitude of
524 oscillations is a function of partition coefficient, where elements with the highest K values
525 exhibit stronger amplitude oscillations, shown here for $\Delta = \pm 3^\circ\text{C}$ case. In comparison with
526 Hf, all other trace elements have lower partition coefficients. During zircon growth the
527 melt in the vicinity of growing zircon becomes less depleted with U, Th and Dy. With an
528 increase in K at lower temperatures (**Fig. 3b**) concentrations of these trace elements in the
529 crystal also increase but to a lesser degree than Y. Overall fluctuations of the
530 concentrations are significantly smaller because of a weaker feedback between the growth
531 rate and trace element partitioning as the system cools.

532

533 **3.6. Effects of major and other accessory mineral crystallization**

534 Next, we consider the influence of another major, minor, or non-zircon accessory
535 mineral crystallization on the outer cell boundary (**Fig. 2**) on the partitioning of trace
536 elements in zircon in the center of melt cell (**Fig. 8d**). The crystallization of plagioclase
537 results in melt cell enrichment in Zr and other trace elements because they are
538 incompatible in plagioclase and most other major minerals such as quartz and sanidine.
539 Crystallization of these major minerals, for the same cooling conditions as is shown in

540 **Figs. 7-8**, results in a larger zircon crystal by a factor of two (as was shown in Fig. 15 of
541 Bindeman and Melnik, 2016). The present study also demonstrates that the crystal
542 becomes enriched in Hf and other incompatible trace elements relative to a model with no
543 major phase crystallization, as these are pushed into the melt cell surrounding zircon by a
544 major phase.

545 The core to rim trace elemental concentrations in zircon change dramatically if co-
546 crystallization of minerals with non-negligible K for the considered elements is involved,
547 such as sphene (for Y), apatite (for P), monazite (for P and LREEs), chevkinite (REEs),
548 and amphibole (MREEs). For example, if sphene and hornblende crystallization is allowed
549 in addition to plagioclase on the outer boundary of our model set up (**Fig. 2**), Y and Dy
550 concentrations in the melt and in zircon drops because last two of these minerals have high
551 partition coefficients for Y and Dy (Bachmann et al., 2005; PetDb.org). It can be noted,
552 however, that the amplitude of elemental concentration oscillations in zircon for elements
553 not entering sphene or hornblende (e.g. Hf) does not strongly depend on their
554 crystallization (**Fig. 7 c vs d**). For elements strongly partitioned into sphene, such as Y,
555 oscillations in zircons are dampened, but still present. This means that the main
556 mechanism responsible for the presence of oscillatory zoning is not the co-crystallization
557 of other minerals, but rather the simple feedback between zircon growth rate and
558 partitioning seen in **Fig 7**.

559

560 **3.7. Water pressure oscillation effects on elemental partitioning in zircon**

561 Another intensive parameter that has been proposed to cause elemental oscillations
562 most notably in plagioclase is water pressure, which strongly affects melt phase diagrams

563 (Bowen, 1928; Sibley et al. 1976) (**Figs. 9-10**). However, changes in water pressure do not
564 directly affect the crystallization of accessory minerals and zircon specifically.
565 Nonetheless, the influence of water pressure oscillations in melt surrounding zircon is
566 non-trivial because of its strong influence on Zr and other element diffusion coefficients
567 (Eq. 5) in water-saturated magmas (**Fig. 9a**), especially at low H₂O contents. As the zircon
568 growth rate is governed by the Zr diffusion coefficient, variations of ~0.2 wt% in the
569 water content lead to changes in the value of the Zr diffusion coefficient by up to a factor
570 of 2 in accordance with Eq. 5 and parametrized results from Watson and Harrison (1983)
571 and Zhang et al. (2010). In contrast, simulations reveal that Hf, P and Dy are less sensitive
572 to variations in water content, while U, Th and Y show stronger oscillations with a
573 frequency governed by water content variations.

574 **Fig. 9b** shows the results of numerical simulations with simultaneous sinusoidal
575 variations in temperature and water content during cooling. We assume that the
576 temperature has 10 oscillations during cooling (e.g. refills by hotter magmas) while water
577 content oscillates 3 times faster (due to convection, or changes in overpressure due to
578 crack propagation). Trace element partitioning is very different in this case. Hf and Dy are
579 only sensitive to temperature oscillations, while U and Th oscillate at the frequency
580 of water content changes. In contrast, two frequencies are clearly seen in P and especially
581 Y. We therefore see that if the X_{H_2O} - T path of growing zircons is more complicated the
582 distribution of trace elements can also show patterns that are difficult to interpret.

583 Oscillatory changes of water concentrations on the order of ± 0.1 wt% in melt are
584 easy to achieve during ± 35 -50 bar pressure oscillations in many shallow, water-saturated
585 magma systems during closed-system degassing (**Fig. 10**). The coexisting gas bubble

586 serves as a medium and a host for water partitioning as is explained in **Fig. 10b-c**. The
587 magnitude of these pressure oscillations is comparable to less than the overpressure
588 changes suggested by many magma systems and is below the cracking limits of rocks
589 (Costa et al. 2012).

590

591

592 **4. Discussion**

593 Numerical experimentation throughout our parameter space confirms our intuitive
594 supposition that oscillatory zoning in zircons cannot be produced by instabilities of
595 boundary layers in respect to monotonic decreases in temperature or water content,
596 crystallization of other minerals nearby, or by interface kinetic reactions such as $Y+P=Zr$
597 $+Si$. Zircon has a nearly constant composition and its growth is governed only by the
598 diffusion of Zr towards the crystal. Due to the large zircon-melt partition coefficient of Zr,
599 growth rates of zircon are much slower than those for plagioclase. Thus, local
600 thermodynamic equilibrium is maintained at the zircon-melt interface. All trace elements
601 diffuse independently due to their low concentrations in the melt and there is no
602 competition between them while partitioning into zircon. In contrast, for a major phase
603 such as plagioclase, oscillatory zoning is caused by albite-anorthite partitioning (Morse,
604 1994) and involves the diffusion of several competing major elements with different
605 diffusivities. Due to large concentrations in the melt, diffusion of major elements is not
606 independent (e.g. Liang et al. 1994) and for plagioclase is described by a diffusion matrix
607 that is also dependent on water (Gorokhova and Melnik, 2010). With much faster
608 plagioclase growth rates, there is a tight relationship between the growth rate and local

609 interface undercooling that is itself strongly dependent on the composition of the boundary
610 layer of plagioclase-compatible elements.

611 Thus, the only way forward to explain pervasive oscillatory zoning of zircon and
612 other accessory minerals is by variations in external intensive parameters: temperature,
613 and for water saturated magmas only, pressure fluctuations, which affects water content-
614 dependent diffusivities in the melt. We demonstrated that small temperature oscillations of
615 only few degrees C can lead to significant variations in Hf and other element content
616 within zircons (**Figs. 7-9**).

617 Our modeling demonstrates that if temperature oscillations are small and
618 frequently spaced along the overall cooling path, oscillatory temperature increases of
619 small magnitude will not lead to zircon dissolution. Small temperature increases of several
620 °C will only temporarily slow down or suspend zircon growth (**Fig. 7**). New layers of
621 zircon will partition trace elements from the immediate boundary layer (**Fig. 4**) in which
622 elements with different diffusivities and partition coefficients will react to zircon boundary
623 advance kinetics, thus recording oscillating temperatures in accordance with each element
624 partition and diffusion coefficient. Our numerical model fundamentally shows that
625 variations in these three parameters: diffusion, partition coefficients, and rate of growth
626 are sufficient to explain the observed features of coeval oscillating elemental variations
627 and predicts that these are to be of similar wavelengths but different amplitude.

628 More prominent oscillations of greater than $\pm 10^{\circ}\text{C}$ will lead to zircon dissolution
629 and recycling of the outer boundary of zircon, but as is outlined above cannot be modeled
630 within the framework of our model. Such phenomena are abundant in nature (e.g. the
631 outer zone on **Fig. 1**; Corfu et al., 2003; Hoskin and Schaltegger, 2003) and are easily

632 recognized by truncated growth boundaries, truncating concentric oscillatory zoning. Our
633 modeling however may put upper limits on the possible temperature oscillations in
634 “simple” zircons in nature of approximately less than 10°C. This suggests that their
635 textural examination by cathodoluminescence and trace element profiling with high spatial
636 resolution can be used to prove their single cooling ($\pm \Delta T$) origin.

637 Our model does not consider non-equilibrium zircon partitioning related to non-
638 trivial Henry’s law constant variations with concentration and temperature (Whitehouse
639 and Kamber, 2002; Hoskin and Schaltegger, 2009). However, we consider that even if
640 present, the above relationships are likely smooth and continuous with temperature and
641 concentration, and cannot be the origin of oscillations, however they can perhaps increase
642 or decrease the amplitudes in proportion to the activity coefficient (γ) variations with
643 concentration ($a=\gamma*C$), and thus K . The main conclusion of the present work is that the
644 simplest model of temperature oscillation of ± 3 to 10°C is already adequate to explain the
645 factor of ~ 2 variations in trace element concentrations within zones as well as the width of
646 those zoning patterns (e.g., **Fig. 1**).

647 Another interesting result of our modeling is that prescribed (Eq. 8) temperature,
648 and/or water content oscillations generate rather smooth oscillatory growth zoning (**Figs.**
649 **7-9**). Similarly, smoothed (not abrupt or step-function) zoning patterns are found in many
650 natural zircons, and may not necessarily require post-growth intracrystalline diffusion.
651 Step-function zoning is commonly assumed to be a result of “rapid” crystallization
652 following dissolution, and is commonly assumed as an initial condition for interdiffusion
653 between adjacent zones in crystals, used in geospidometry and crystal residence studies.

654 Instead, we find that these patterns may result from precisely the opposite: a system with
655 slow zircon growth driven by slow cooling rates in a large pluton.

656

657 **5. Implications for magmatic systems**

658 Small temperature variations could be a consequence of convection in large and
659 slowly cooling magmatic bodies, and oscillatory zoning in crystals has traditionally been
660 interpreted to reflect such processes. Bowen (1928) suggested that oscillatory zoning in
661 plagioclase may be related to convection in the magma chamber whereby each crystal
662 travels through a diversity of temperatures and pressures in a cyclical fashion, a model
663 which remains popular today. As crystals may have different trajectories in temperature,
664 time, and space before being assembled by magma mixing into a single hand specimen,
665 zoning patterns of neighboring crystals may differ. **Figure 10** presents a cartoon view of a
666 magma chamber with mushy and liquid parts that may experience of temperature and
667 pressure increases due to replenishments by hotter magmas from below causing
668 compositional and thermal convection, which may also affect the P-T condition
669 experienced by any given crystal.

670 Besides variations in temperature, oscillations in fluid pressure have long been
671 called upon to explain plagioclase zoning (Bowen, 1928; Morse, 1994), but such effects
672 will not directly be applicable to zircon and other accessory phases as these do not affect
673 saturation and partitioning relations (**Fig. 3b**). However, as we demonstrated above,
674 variations in fluid pressure affect zircon oscillatory zoning comes in a less trivial way via
675 oscillations of X_{H_2O} in the melt surrounding the zircon, which affects the diffusion
676 coefficients of Zr and other trace elements. This water effect is stronger at low water

677 concentrations as the effect of water on diffusion is the strongest for the first 0.3 wt%
678 increase in water compared to a subsequent 3 wt% water increase (Watson and Harrison,
679 1983).

680 This control by water is possible only for water-saturated shallow magma bodies
681 (gas bubble in **Fig. 11b**), where external pressure variations are transmitted to water
682 concentrations in melt causing water to diffuse in and out of gas bubbles. For example,
683 magma bodies located in the shallow crust a few kilometers deep (equivalent to 0.3-0.5
684 kbar pressure) will be water saturated with C_{H_2O} between 2-3wt% (Newman and
685 Lowenstern, 2002).

686 Many shallow magma bodies, including the Bishop and Fish Canyon Tuffs were
687 likely water-saturated (Anderson et al. 2000; Bachmann et al. 2002). Such compressible
688 magma bodies are capable of sustaining pressure variations on the order of ± 35 -50 bars
689 due to: rejuvenation, eruptions, dike formation, and perhaps external tectonic forces as is
690 portrayed in **Fig. 11**. Pressure increases followed by thermal and viscous relaxation will
691 cause water to migrate in and out of gas bubble a melt cell, in turn causing the zircon to
692 develop oscillations. Coupled temperature and pressure oscillations of different
693 frequencies (**Figs. 9-10**) will cause non-monotonic oscillations of different wavelengths,
694 which will be variable for each element. For water-saturated or undersaturated magma
695 bodies an alternative scenario may involve H_2O and CO_2 fluxing of more static magma
696 mushes, causing variations in X_{H_2O} .

697 Our modeling confirms that prominent oscillatory zoning should characterize near-
698 solidus $\sim 700^\circ C$ plutonic and mush-related zircons, commonly from cold and wet
699 environments as compared to $> 800^\circ C$ hot and dry, water-saturated rhyolites, which show

700 more subdued oscillatory zoning (e.g., **Fig. 1, Fig A1** supplementary, Claiborne et al.,
701 2010 vs. Carley et al. 2011). To illustrate this point, our imaging of the trace element
702 distribution in zircons from Fish Canyon tuff (cold, ~750°C), Toba (hotter, ~780°C), and
703 Yellowstone (hot, ~850°C) systems (Loewen and Bindeman, 2016, **Figs. 1, A1**) supports
704 this point. The example for the cold system is the Spirit Mountain Batholith studied by
705 Claiborne et al. (2010) which has cores are not zoned while the rims have oscillatory
706 zoning, in line with our **Fig. 8-9**. Hot Icelandic rhyolites (Carley et al. 2011) are similar to
707 Yellowstone-Snake River Plain rhyolites in dull cathodoluminescence images and a lack of
708 oscillations (e.g. Watts et al., 2012; Colón et al. 2015).

709 Temperature fluctuations may be the result of pluton formation by multiple dike-
710 sill injections (Annen et al. 2006), and our companion paper modeled these effects on
711 zircon growth and dissolution (Bindeman and Melnik, 2016). We observed that with an
712 increase in distance from a sill injection zone, the amplitude of temperature disturbances
713 in a zircon-bearing parcel of magma or rock will progressively decrease along with the
714 sharpness of the temperature fronts. This will result in less pronounced oscillatory zones
715 towards the rim of zircons away from the oscillating heat source (“hot zone”).

716 Finally, our modeling provides some instruction for rapidly improving in situ
717 analysis of zircons with micron to submicron spatial resolution. The scale of zoning that
718 we recover from our modeling ranges from 1 to 10 μm (**Fig 7-9**) and the amplitude of
719 variation is less than a factor of two. Therefore, our modeling provides guiding principles
720 for modern methods for zircon microanalysis. Such studies should therefore provide
721 adequate characterization of the evolution of magmatic systems using the accessory
722 minerals.

723

724 **Acknowledgements.** OEM acknowledge support from the Russian Foundation for Basic
725 Research (RFBR, grant number 15-01-02639), and the University of Oregon Meierjurgan
726 and Global Oregon Faculty Collaboration Fund for funding this research. INB
727 Acknowledges support from NSF grant 1447337. We thank Dylan Colón and Mike Hudak
728 for edits and comments, Calvin Miller, and two anonymous reviewers for reviews, and
729 Renat Almeev and Keith Putirka for editorial comments.

730

731 **REFERENCES**

- 732 Annen, C., Blundy, J.D., Sparks, and R.S.J. (2006) The genesis of intermediate and silicic
733 magmas in deep crustal hot zones. *Journal of Petrology* 47 (3), 505-539
- 734 Aranovich, L. Ya., Bortnikov N.S., T. F. Zinger, S. E. Borisovskiy, V. A. Matrenichev,
735 A. N. Pertsev, E. V. Sharkov, and S. G. Skolotnev (2018). Morphology and Impurity
736 Elements of Zircon in the Oceanic Lithosphere at the Mid-Atlantic Ridge Axial
737 Zone (6°–13° N): Evidence of Specifics of Magmatic Crystallization and
738 Postmagmatic Transformations *Petrology*, 2017, Vol. 25, No. 4, pp. 339–364.
- 739 Bacon, C.R. (1989) Crystallization of accessory phases in magmas by local saturation
740 adjacent to phenocrysts. *Geochimica et Cosmochimica Acta* 53 (5), 1055-1066.
- 741 Bachmann, O., Dungan, M. A. & Lipman, P. W. (2002). The Fish Canyon magma body,
742 San Juan volcanic field, Colorado: Rejuvenation and eruption of an upper crustal
743 batholith. *Journal of Petrology* 43, 1469–1503.
- 744 Bachmann, O., Dungan, M. A., & Bussy, F. (2005). Insights into shallow magmatic
745 processes in large silicic magma bodies: The trace element record in the fish
746 canyon magma body, Colorado. *Contributions to Mineralogy and Petrology*,

- 747 149(3), 338-349. doi:<http://dx.doi.org/10.1007/s00410-005-0653-z>
- 748 Bindeman, I.N., and Melnik, O.E. (2016) Zircon survival, rebirth and recycling during
749 crustal melting, magma crystallization, and mixing based on numerical modelling.
750 Journal of Petrology, 57, 437-460.
- 751 Boehnke, P., Watson, E.B., Trail, D., Harrison, T.M., and Schmitt, A.K. (2013) Zircon
752 saturation re-revisited. Chemical Geology 351, 324-334.
- 753 Bowen, N.L. (1928) The Evolution of the Igneous Rocks. 334 p., Princeton Univ. press,
754 Princeton, New Jersey.
- 755 Bunsen R.W. (1851) Über die Prozesse der vulkanischen Gesteinsbildungen Islands.
756 Annual Review of Physical Chemistry, 83,197–272.
- 757 Carley T.L., Miller C.F., Wooden J.L., Bindeman I.N., and Barth A.P. (2011) Zircon from
758 historic eruptions in Iceland: Reconstructing storage and evolution of silicic
759 magmas: Mineralogy and Petrology, 102, 135-161.
- 760 Cherniak D.J., Hanchar J.M., and Watson E.B. (1997a) Rare-Earth diffusion in zircon.
761 Chemical Geology, 134, 289–301
- 762 Cherniak D.J., Hanchar J.M., and Watson E.B. (1997b) Diffusion of tetravalent cations in
763 zircon. Contribution to Mineralogy and Petrology, 127,383–390
- 764 Claiborne L.L., Miller C.F., Gualda G.A.R., Carley T.L. Covey A.K. Wooden J.L. and
765 Fleming M.A. (2017) Zircon as magma monitor: Robust, temperature-dependent
766 partition coefficients from glass and zircon surface and rim measurements from
767 natural systems. AGU Book series, accepted
- 768 Claiborne, L.L., Miller, C.F., and Wooden, J.L. (2010) Trace element composition of
769 igneous zircon: a thermal and compositional record of the accumulation and

- 770 evolution of a large silicic batholith, Spirit Mountain, Nevada. Contributions to
771 Mineralogy and Petrology, 160, 511.
- 772 Colón, D.P., Bindeman, I.N., Ellis, B.S., Schmitt, A.K., and Fisher, C.M. (2015)
773 Hydrothermal alteration and melting of the crust during the Columbia River
774 Basalt-Snake River Plain transition and the origin of low- $\delta^{18}\text{O}$ rhyolites of the
775 central Snake River Plain. *Lithos*, 224-225: 310-323
- 776 Corfu, F., Hanchar, J.M., Hoskin, P.W.O., and Kinny, P. (2003) Atlas of zircon textures.
777 in *Zircon, Reviews in Mineralogy and Geochemistry*, 53 (1), 469-500,
- 778 Costa, F., Chakraborty, S., Dohmen, R. (2003) Diffusion coupling between trace and
779 major elements and a model for calculation of magma residence times using
780 plagioclase. *Geochimica et Cosmochimica Acta*, 67, 2189–2200.
- 781 Crowley, J.L., and Bowring S.A. Hanchar J.M. (2006) What is a magma crystallization
782 age? Insight from micro-sampling of chemical domains in zircon from the Fish
783 Canyon Tuff. *GCA* 10.1016/j.gca.2006.06.153
- 784 De Hoog J.C.M., Lissenberg C.J., Brooker R.A., Hinton R., Trail D., Hellebrand E.W.G.,
785 and Brooker R.A. (2014) Hydrogen incorporation and charge balance in natural
786 zircon. *Geochimica et Cosmochimica Acta*, 141, 472–486.
- 787 Finch, R.J., Hanchar, J.M., Hoskin, P.W.O., and Burns P.C. (2001) Rare-earth elements in
788 synthetic zircon: Part 2. A single-crystal X-ray study of xenotime substitution .
789 *American Mineralogist*, 86, 681–689.
- 790 Fu B., F. Page Z., Cavosie A., Fournelle, J. Kita, N., Lackey J.S., Wilde S., and Valley,
791 J.W. (2008) Ti-in-zircon thermometry: applications and limitations. Contributions
792 to *Mineralogy and Petrology*, 156, 197–215.

- 793 Ghiorso M. S. and Sack R.O. (1995). Chemical mass-transfer in magmatic processes IV:
794 A revised and internally-consistent thermodynamic model for the interpolation and
795 extrapolation of liquid–solid equilibria in magmatic systems at elevated
796 temperatures and pressures. *Contributions to Mineralogy and Petrology* 119, 197–
797 212.
- 798 Gorokhova N.V. and Melnik O. (2010) Modeling of the dynamics of diffusion crystal
799 Hahn, M., Behrens H., Tegge-Schüring A., Koepke J., Horn I., Rickers K.,
800 Falkenberg G. and Wiedenbeck M. (2005) Trace element diffusion in rhyolitic
801 melts: comparison between synchrotron radiation X-ray fluorescence
802 microanalysis (μ -SRXRF) and secondary ion mass spectrometry (SIMS). *Eur. J.*
803 *Min.* 17: 233-242.
- 804 Hanchar J.M., and van Westrenen W. (2007) Rare Earth Element Behavior in Zircon-Melt
805 Systems. *ELEMENTS*, 3(1), 37-42.
- 806 Hanchar, J.M., Finch, R.J., Hoskin, P.W.O., Watson, E.B., Cherniak, D.J., and Mariano,
807 A.N. (2001) Rare earth elements in synthetic zircon. 1. Synthesis and rare earth
808 element and phosphorus doping. *American Mineralogist*, 86, 667-680.
- 809 Harrison, T.M., and Watson, E.B. (1984) The behavior of apatite during crustal anatexis:
810 equilibrium and kinetic considerations. *Geochimica et Cosmochimica Acta*, 48 (7),
811 1467-1477.
- 812 Harrison, T.M., and Watson, E.B. (1983) Kinetics of zircon dissolution and zirconium
813 diffusion in granitic melts of variable water content. *Contributions to Mineralogy*
814 *and Petrology*, 84, 66-72.

- 815 Hofmann A.E., Valley JW, Watson E.B., Cavosie A.J., and Eiler J.M. (2009) Sub-micron
816 scale distributions of trace elements in zircon. *Contributions to Mineralogy and*
817 *Petrology*, 158, 317–335.
- 818 Hoskin, P.W.O. and Schaltegger, U. (2003) The composition of zircon and igneous and
819 metamorphic petrogenesis. In: Hanchar JM, Hoskin PWO (eds) *Zircon. Reviews in*
820 *Mineralogy and Geochemistry*, 53, 27–62.
- 821 Hayden L.A. and Watson E.B. (2007) Rutile saturation in hydrous siliceous melts and its
822 bearing on Ti-thermometry of quartz and zircon. *Earth and Planetary Science*
823 *Letters*, 258, 561–568.
- 824 Lasaga, A.C.(1982). Towards a master equation in crystal growth. *American Journal of*
825 *Science*, 282, 1264-1288.
- 826 Lipman, P.W. (2007) Incremental assembly and prolonged consolidation of Cordilleran
827 magma chambers: *Geosphere*, v. 3, p. 42–70, doi:10.1130/GES00061.1.
- 828 Loewen M.W., Bindeman I.N. (2016) Oxygen isotope thermometry reveals high magmatic
829 temperatures and petrogenetic differences between hot-dry Yellowstone/ Snake River
830 Plain and Icelandic rhyolites compared to cold-wet systems. *American*
831 *Mineralogist*, 101, 1222-1227. DOI: 10.2138/am-2016-5591
- 832 Loewen M., Bindeman I.N., Melnik O. (2016) Eruption mechanisms and short duration of
833 large rhyolitic lava flows of Yellowstone. *Earth and Planet Sci Lett*, DOI:
834 10.1016/j.epsl.2016.10.034
- 835 L'Heureux,I. (1993) Oscillatory zoning in crystal growth: a constitutional undercooling
836 mechanism. *Physical Review E*, 48, 4460-4469.
- 837 Marshall, D.J. (1988) *Catholuminescence of Geological Materials*. 146 p., Unwin Hyman,.
838 Boston, London, Sydney, Wellington.

- 839 Morse SA (1994) Basalts and Phase Diagrams: An Introduction to the Quantitative Use of
840 Phase Diagrams in Igneous Petrology, Krieger Publishing Company, 493 pages
- 841 Neogi S. Edward W. Bolton E.W., Chakraborty S. (2014) Timescales of disequilibrium
842 melting in the crust: constraints from modelling the distribution of multiple trace
843 elements and a case study from the Lesser Himalayan rocks of Sikkim. *Contrib.*
844 *Mineral Petrol.* 168: 1-22, [10.1007/s00410-014-1020-8](https://doi.org/10.1007/s00410-014-1020-8)
- 845 Mungall, J. Dingwell, D.B. and Chaussidon, M. (1999) Chemical diffusivities of 18 trace
846 elements in granitoid melts. *Geochimica et Cosmochimica Acta*, 63, 2599-2610.
- 847 Piwinski, A. J. (1968) Experimental studies of igneous rock series: Central Sierra Nevada
848 Batholith, California. *Journal of Geology*, 76, 548-570.
- 849 Rubatto, D. and Hermann, J. (2007) Experimental zircon/melt and zircon/garnet trace
850 element partitioning and implications for the geochronology of crustal rocks.
851 *Chemical Geology*, 241, 38–61.
- 852 Rustad, J. (2015) Interaction of rhyolite melts with monazite, xenotime and zircon
853 surfaces. *Contributions to Mineralogy and Petrology*, 169, 50–58.
- 854 Sano Y., Terada K., and Fukuoka T. (2002) High mass resolution ion microprobe analysis
855 of rare earth elements in silicate glass, apatite and zircon: lack of matrix
856 dependency. *Chemical Geology*, 184 (3), 217-230
- 857 Shore, M. and Fowler, A.D. (1996) Oscillatory zoning in minerals: A common
858 phenomenon. *Canadian Mineralogist*, 34, 1111-1126.
- 859 Sibley, D.F., Vogel, T.A., Walker, B.M. and Byerly, G. (1976) The origin of oscillatory
860 zoning in plagioclase: a diffusion and growth controlled model. *American Journal*
861 *of Science*, 16, 275-284.

- 862 Sparks, R.S.J., and Cashman K.V. (2017) Dynamic Magma Systems: Implications for
863 Forecasting Volcanic Activity Elements, 13, p. 35-40. DOI: 10.2113/gselements.13.1.35
- 864 Trail, D., Cherniak, D.J., Watson, E.B., Harrison, T.M. , Weiss, B.P., and Szumila, I.
865 (2016) Li zoning in zircon as a potential geospeedometer and peak temperature
866 indicator. Contributions to Mineralogy and Petrology, 171, 25.
- 867 Vance J.A. (1962) Zoning in igneous plagioclase: normal and oscillatory zoning.
868 American Journal of Science, 260, 746–760.
- 869 Wallace, G. S. and Bergantz, G. W. (2002) Wavelet based correlation (WBC) of zoned
870 crystal populations and magma mixing, Earth and Planetary Science Letters, 202,
871 133-145.
- 872 Watson, E. B., and Liang, Y. (1995) A simple model for sector zoning in slowly grown
873 crystals: Implications for growth rate and lattice diffusion, with emphasis on
874 accessory minerals in crustal rocks. American Mineralogist, 80(11-12), 1179-1187.
- 875 Watson, E.B., and Muller, T. (2009) Non-equilibrium isotopic and elemental fractionation
876 during diffusion-controlled crystal growth under static and dynamic conditions.
877 Chemical Geology, 267, 111-124.
- 878 Watson E.B. (1996) Surface enrichment and trace-element uptake during crystal growth.
879 Geochimica et Cosmochimica Acta, 60, 5013-5020.
- 880 Watson, E.B. (1980) Some experimentally-determined zircon/liquid partition coefficients
881 for the rare earth elements. Geochimica et Cosmochimica Acta, 44, 895-897.
- 882 Watson, E.B. and Harrison, T.M. (1983) Zircon saturation revisited: temperature and
883 compositional effects in a variety of crustal magma types. Earth and Planetary
884 Science Letters, 64, 295-304.

- 885 Watson, E.B., D.A. Wark, and Thomas, J.B.(2006) Crystallization thermometers for
886 zircon and rutile. *Contribution to Mineralogy and Petrology*, 151, 413-433.
- 887 Watts, K.E., Bindeman, I.N. and Schmitt, A.K. (2012) Crystal-scale anatomy of a dying
888 supervolcano: An isotope and geochronology study of individual phenocrysts from
889 voluminous rhyolites of the Yellowstone caldera. *Contributions to Mineralogy and
890 Petrology*, 164, 45-67
- 891 Whitehouse M.J., and Kamber B.S. (2002) On the overabundance of light earth elements
892 in terrestrial zircons and its implication for Earth's earliest magmatic
893 differentiation. *Earth and Planetary Science Letters*, 204,333-346
- 894 Wiebe, R.A. (1968) Plagioclases stratigraphy: record of magmatic conditions and events
895 in a granitic stock. *American Journal of Science*, 266, 690-703.
- 896 Zhang, Y.X., Ni, H., and Chen, Y. (2010) Diffusion data in silicate melts. in: Zhang Y.,
897 Cherniak D.J. (Eds), *Diffusion in minerals and melts. Reviews in Mineralogy and
898 Geochemistry*, 72, 313-408.
- 899

900 **Fig. Captions**

901 **Fig. 1** Cathodoluminescence (CL) image and trace element profiles through a zircon
902 crystal in Early Fish Canyon Tuff. Profile is from the rim to the core. Dark areas in the CL
903 image dark areas generally correspond to higher concentrations of trace elements. The
904 magnitude of oscillatory zoning is within a factor of two. To a first order there are
905 correlations between greyscales and changes in concentrations. Large increases in Y and P
906 concentrations likely reflect the co-crystallization and dissolution of sphene and apatite
907 that are present in the assemblage. The total number of zones is 20-25 reflecting episodes
908 of thermal perturbation. Data collected on a Cameca 100 Electron microprobe by John
909 Donovan (University of Oregon) using 100 kV voltage, 400 nA current, and collections in
910 four detectors. Beam diameter is 1-2 μm , detection limits are 0.001-0.006 wt%, relative
911 error for each data point is ~2-5%, and the lowest concentrations of P are close to the
912 detection limit.

913 **Fig 2.** Model set up with two moving boundaries. Upon cooling, zircon grows at a rate V
914 determined by the saturation conditions and the rate of temperature change. Local
915 thermodynamic equilibrium is assumed. The concentration of Zr (C_{Zr}) at the crystal-melt
916 interface is a function of temperature, while the concentrations of trace elements (C_{tr}) are
917 governed by the zircon-melt partition coefficients K . The crystallization of melt around the
918 zircon at rate W may partition elements in accordance with the bulk partition coefficient k .
919 This will lead to either an enrichment or depletion wave in the melt cell that propagates
920 towards the growing zircon. The melt cell has a T - X phase diagram defined by the user,
921 and it determines the rate W of melt cell expansion or contraction as a function of

922 temperature and time. C and C_X are the concentration of Zr and trace element in the melt
923 and major minerals, respectively.

924 **Fig. 3** Model input parameters, diffusion and partition coefficients. **(a)** Compilation of
925 diffusion coefficients of relevant elements in a metaluminous rhyolitic melt, shown here
926 for 3 wt.% water following sources cited in Zhang et al. (2010), the parametrization of T
927 and X_{H_2O} is given in Eq. 5a in the text. **(b)** Trace element partitioning coefficients as a
928 function of temperature, most data is compiled from Rubatto and Hermann (2007) and
929 checked against the natural data of Claiborne et al. (2017). For Zr saturation Eq. 5b is
930 used. Expressions for trace element diffusion and partition coefficients can be found in the
931 supplementary MATLAB code (functions TraceDiff and Kdd, respectively).

932 **Fig 4.** Trace element profiles in melt surrounding a growing zircon crystal after 5000
933 years of linear cooling from 840°C to 720°C in a melt cell with a radius 2 mm. Notice
934 variable amplitudes of depletion of the boundary layer around zircon for the indicated
935 trace elements, the width and the level of depletion is a function of both the diffusion
936 coefficient and the partition coefficient. Slower diffusion and a high partition coefficient
937 (e.g. Hf) expectedly generates the widest and deepest depletion (e.g. Hf), while fast
938 diffusion (Y, Dy), and/or a smaller partition coefficient (P) generates a narrower boundary
939 layer. Elements are normalized to their far-field concentration in the melt.

940 **Fig 5.** Trace element concentration profiles in zircon after a linear cooling from 840° to
941 720°C over 5000 years in a melt cell with a radius 2 mm and without co-crystallization of
942 other minerals on the outer boundary of the cell. Smooth changes of concentrations are
943 determined by partition coefficients and by the rate of zircon growth. Slower cooling of
944 zircon generates different concentration profiles and levels of enrichment/depletion. In

945 particular, Hf concentration in zircon increases with slower cooling (see also **Fig. 7**
946 below).

947 **Fig. 6.** Normalized concentration of xenotime, YPO_4 , in zircon as a function of zircon
948 radius for a linear temperature drop and different values of the xenotime partition
949 coefficient, K_X , assuming no independent partitioning of P and Y into zircon ($K_P = K_Y = 0$).
950 Decreases in xenotime concentration in zircon are primarily controlled by decreases in Y
951 in the boundary layer, while P remains nearly constant in the vicinity of the crystal-melt
952 interface (**Fig. 4**). Notice the lack of oscillations due to the xenotime substitution
953 mechanism.

954 **Fig. 7.** Effects of temperature oscillations of $\pm 3^\circ\text{C}$ superimposed on cooling of different
955 rates and duration. Cell size radius is 2 mm. **(a)** Zircon radius, **(b)** growth rate, **(c)** Hf and
956 **(d)** Y concentrations. The legend in **(a)** applies to all graphs and gives the total length of
957 cooling from 840 to 720°C in kyr. Notice that 3°C temperature increases do not cause
958 zircon dissolution but slow down zircon growth **(a, b)**, that the amplitude and width of
959 oscillations is better pronounced for the longer duration of cooling in **(c and d)**, and that
960 faster cooling promotes decreases in Hf concentrations while slow cooling results in a core
961 to rim increases in Hf concentrations, see text for discussion.

962 **Fig. 8** Concentrations of trace elements vs zircon radius at $\pm 3^\circ\text{C}$ for various cooling rates
963 and crystallization scenarios. Cooling is linear from 840°C to 720°C for 0.5, 5, and 50 kyr
964 **(a-c)** with $\pm 3^\circ\text{C}$ sinusoidal temperature oscillations as in **Fig. 7a**. In a-c, melt is
965 crystallizing only zircon. **(d)** Influence of amphibole and sphene co-crystallization on the
966 outer cell boundary (**Fig. 2**) leading to decreases in Y and Dy concentrations in zircon.

967 **Fig. 9a.** Concentration of trace elements vs zircon radius with water content oscillations.
968 The latter can be result of the convection of a zircon+bubble melt pocket, pressure
969 oscillations, and H₂O and CO₂ fluxing as is explained in **Fig. 10.** (a) Monotonic cooling is
970 from 840°C to 720°C for 5 kyr with water content oscillation of 3±0.1 wt%.
971 (b) The same as **Fig. 9a** but with sinusoidal temperature and water content variations and
972 with the frequency of water content variation of 3 times faster than the temperature
973 oscillations for the temperature. Notice that the width and amplitude of the oscillatory
974 zones becomes decoupled for different elements as a function of their diffusivities at
975 different water content, and partitioning relations.

976 **Fig 10.** Cartoon explaining possible causes of temperature and water content oscillations
977 in a water-saturated melt ($P_{total} = P_{H2O}$) surrounding zircon, affecting its growth and
978 partitioning relations (**Fig. 9**). (a) Magma chamber that can sustain ΔP pressure
979 oscillations of 50 bar without eruption due to recharge from below and dike formation
980 from above; convection of 150 m in the vertical dimension ($\pm\rho gh$) is additionally capable
981 of 50 bar pressure variations. (b) Zircon, plagioclase and a gas bubble within a melt cell
982 with externally controlled pressure affecting water solubility in the melt and the diffusion
983 of Zr and other trace elements. (c) Effects of 35-50 bar pressure oscillations on water
984 content in the melt during closed system degassing into an internal bubble, calculated in
985 VolatiteCalc (Newman and Lowenstern, 2002).

